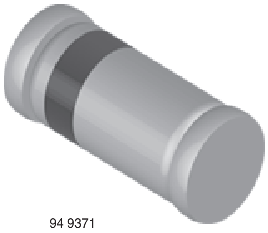
Fast Switching Diode

Features

- Silicon Epitaxial Planar Diodes
- Electrical data identical with the devices 1N4148 and 1N4448 respectively



Applications

Extreme fast switches

Mechanical Data

Case: MiniMELF Glass Case (SOD-80C)
Weight: approx. 30.8 mg

Cathode Band Color:
Packaging Codes/Options:
GS18 / 10 k per 13" reel (8 mm tape), 10 k/box
GS08 / 2.5 k per 7" reel (8 mm tape), 12.5 k/box

Parts Table

Part	Type differentiation	Ordering code	Remarks
LL4148	V_{RRM} = 100 V, V_F @ I_F 50 mA < 1 V, Single Diodes	LL4148-GS18 or LL4148-GS08	Tape and Reel
LL4448	V_{RRM} = 100 V, V_F @ I_F 100 mA < 1 V, Single Diodes	LL4448-GS18 or LL4448-GS08	Tape and Reel

Absolute Maximum Ratings

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Repetitive peak reverse voltage		V_{RRM}	100	V
Reverse voltage		V_R	75	V
Peak forward surge current	t_p = 1 µs	I_{FSM}	2	A
Repetitive peak forward current		I_{FRM}	500	mA
Forward current		I_F	300	mA
Average forward current	V_R = 0	I_{FAV}	150	mA
Power dissipation		P_V	500	mW

Thermal Characteristics

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Junction ambient	on PC board 50 mm x 50 mm x 1.6 mm	R_{thJA}	500	K/W
Junction temperature		T_j	175	°C
Storage temperature range		T_{stg}	- 65 to + 175	°C

Electrical Characteristics

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Forward voltage	I_F = 5 mA	V_F	0.62		0.72	V
	I_F = 50 mA	V_F		0.86	1	V
	I_F = 100 mA	V_F		0.93	1	V
Reverse current	V_R = 20 V	I_R			25	nA
	V_R = 20 V, T_j = 150 °C	I_R			50	µA
	V_R = 75 V	I_R			5	µA
Breakdown voltage	I_R = 100 µA, t_p/T = 0.01, t_p = 0.3 ms	$V_{(BR)}$	100			V
Diode capacitance	V_R = 0, f = 1MHz, V_{HF} = 50 mV	C_D			4	pF
Rectification efficiency	V_{HF} = 2 V, f = 100 MHz	η_r	45			%
Reverse recovery time	$I_F = I_R$ = 10 mA, i_R = 1 mA	t_{rr}			8	ns
	I_F = 10 mA, V_R = 6 V, $i_R = 0.1 \times I_R$, R_L = 100 Ω	t_{rr}			4	ns

Typical Characteristics (T_{amb} = 25 °C unless otherwise specified)

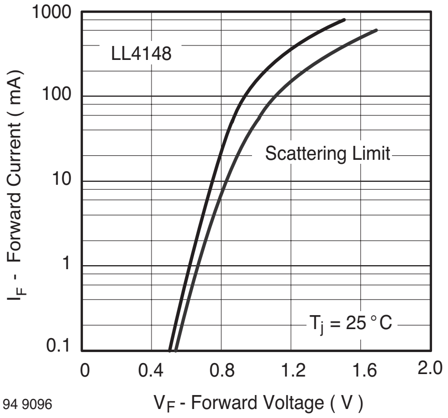


Fig. 1 Forward Current vs. Forward Voltage

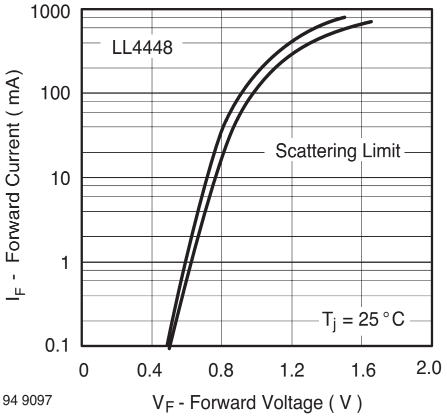


Fig. 2 Forward Current vs. Forward Voltage

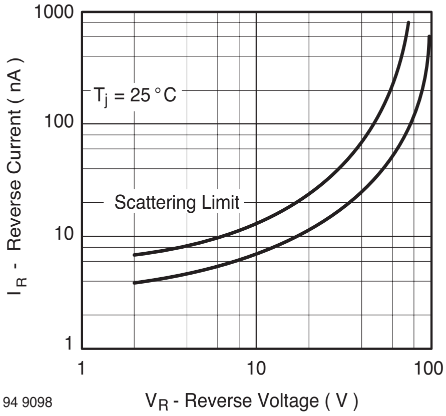


Fig. 3 Reverse Current vs. Reverse Voltage

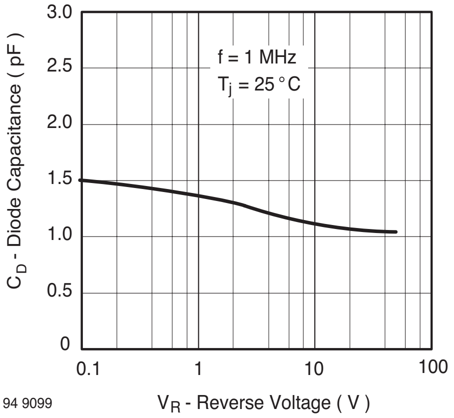
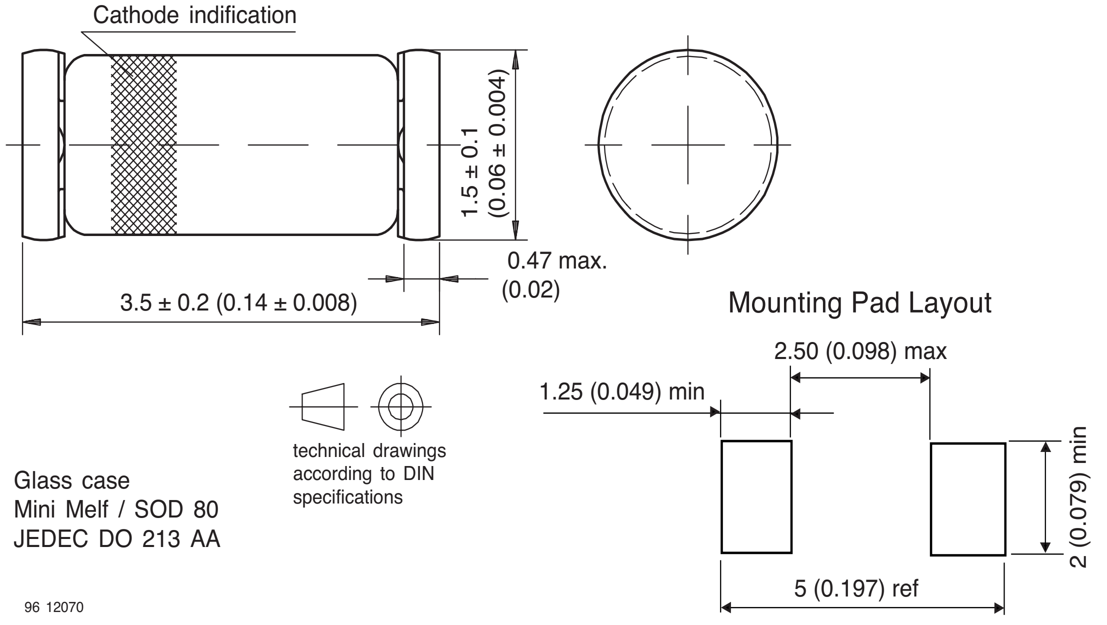


Fig. 4 Diode Capacitance vs. Reverse Voltage

Package Dimensions in mm (Inches)



Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operatingsystems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany
Telephone: 49 (0)7131 67 2831, Fax number: 49 (0)7131 67 2423